
2SC3836

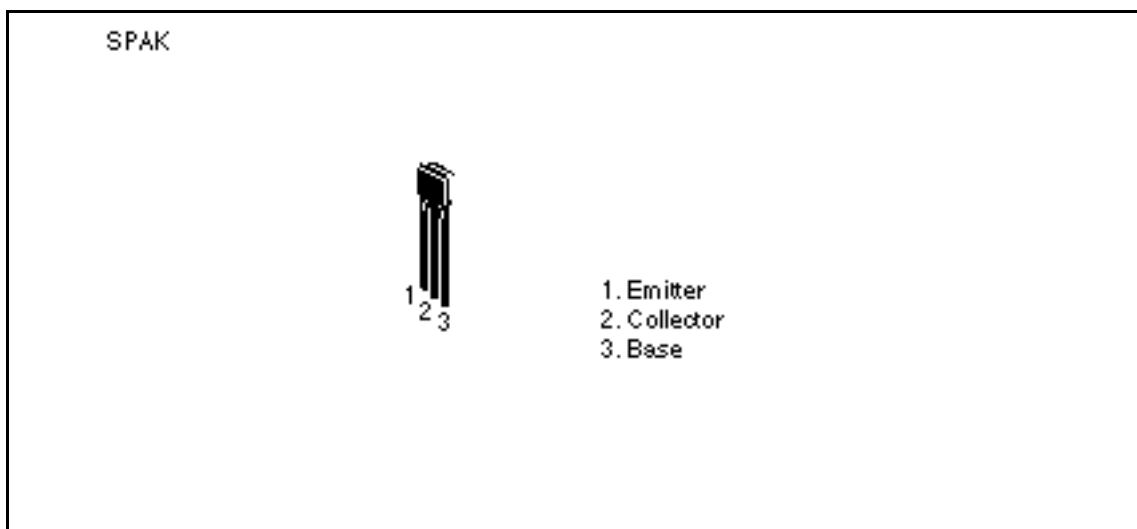
Silicon NPN Epitaxial

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Application

Low frequency amplifier, switching

Outline



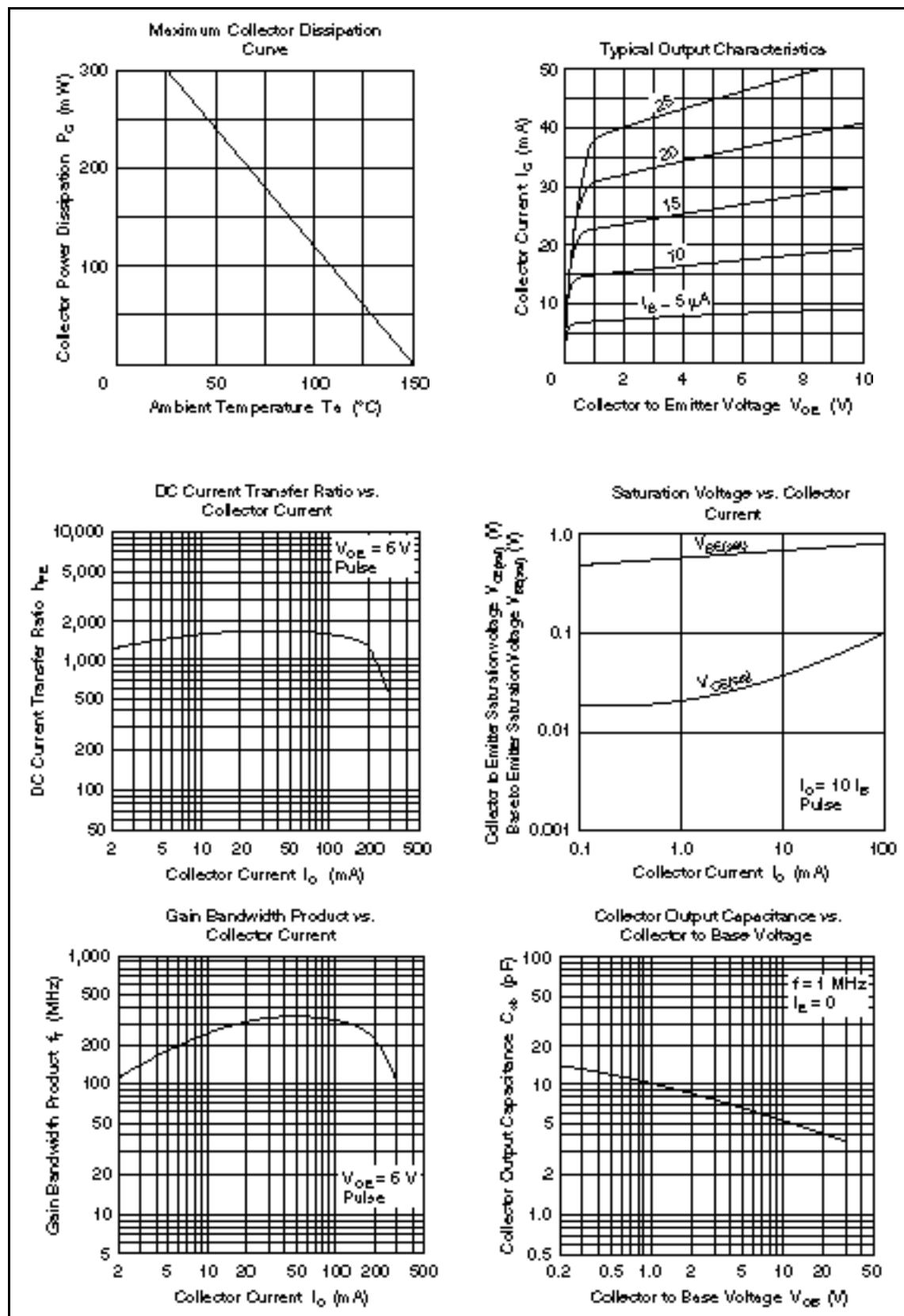
Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	60	V
Collector to emitter voltage	V_{CEO}	50	V
Emitter to base voltage	V_{EBO}	15	V
Collector current	I_C	300	mA
Collector power dissipation	P_C	300	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

2SC3836

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	60	—	—	V	$I_C = 10\ \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	50	—	—	V	$I_C = 1\ mA, R_{BE} =$
Emitter to base breakdown voltage	$V_{(BE)EBO}$	15	—	—	V	$I_E = 10\ \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	1	μA	$V_{CB} = 50\ V, I_E = 0$
Base to emitter voltage	V_{BE}	—	—	0.75	V	$V_{CE} = 6\ V, I_C = 1\ mA$
DC current transfer ratio	h_{FE1}	800	—	2000		$V_{CE} = 6\ V, I_C = 100\ mA$ (pulse test)
	h_{FE2}	500	—	—		$V_{CE} = 6\ V, I_C = 1\ mA$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	0.3	V	$I_C = 300\ mA, I_B = 30\ mA$ (pulse test)



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